SQ2303CES

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Automotive P-Channel 30 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

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P-Channel MOSFET



COMPLIANT HALOGEN

Marking Code: TAYXX

PRODUCT SUMMARY				
V _{DS} (V)	-30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 V$	0.170			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.370			
I _D (A)	-2.5			
Configuration	Single			

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2303CES (for detailed order number please see <u>www.vishay.com/doc?79771</u>)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-30	V	
Gate-source voltage		V _{GS}	± 20		
Continuous drain current	T _C = 25 °C	I	-2.5		
	T _C = 125 °C	- I _D	-1.5		
Continuous source current (diode conduction)		I _S	-2.4	A	
Pulsed drain current ^a		I _{DM}	-10		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-7		
Single pulse avalanche energy		E _{AS}	2.4	mJ	
Maximum power dissipation	T _C = 25 °C	PD	1.9	w	
	T _C = 125 °C		0.6	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^b	R _{thJA}	175	°C/W	
Junction-to-case (drain)		R _{thJF}	78	0/10	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. When mounted on 1" square PCB (FR-4 material)

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static					•			
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$		-30	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		-1.5	-2.0	-2.5	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -30 V	-	-	-1		
		$V_{GS} = 0 V$	V _{DS} = -30 V, T _J = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	V _{DS} = -30 V, T _J = 175 °C	-	-	-150		
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-8	-	-	Α	
Drain-source on-state resistance ^a	(- <i>)</i>	V _{GS} = -10 V	I _D = -1.7 A	-	0.130	0.170	- Ω	
	_	V _{GS} = -10 V	I _D = -1.7 A, T _J = 125 °C	-	-	0.247		
	R _{DS(on)}	V _{GS} = -10 V	I _D = -1.7 A, T _J = 175 °C	-	-	0.288		
		V _{GS} = -4.5 V	I _D = -1.3 A	-	0.280	0.370		
Forward transconductance b	9 _{fs}		= -5 V, I _D = -1.7 A	-	4	-	S	
		Dynamic ^b	-			1		
Input capacitance	Ciss	V _{GS} = 0 V	V _{DS} = -25 V, f = 1 MHz	-	175	210	pF	
Output capacitance	C _{oss}			-	44	50		
Reverse transfer capacitance	C _{rss}			-	29	35		
Total gate charge ^c	Qg			-	4.7	6.8		
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V	V _{DS} = -15 V, I _D = -1.7 A	-	1.0	-	nC	
Gate-drain charge ^c	Q _{qd}	-			1.1	-		
Gate resistance	R _q	f = 1 MHz		3.12	6.25	18.12	Ω	
Turn-on delay time ^c	t _{d(on)}				6	8	- ns	
Rise time ^c	t _r	V_{DD} = -15 V, R _L = 8.8 Ω I _D \cong -1.7 A, V _{GEN} = -10 V, R _g = 1 Ω		-	8	12		
Turn-off delay time ^c	t _{d(off)}			-	13	18		
Fall time ^c	t _f			-	8	12		
	Source-Drain [Diode Ratings and	d Characteristics ^b	L		1		
Pulsed current ^a	I _{SM}	_		-	-	-10	Α	
Forward voltage	V _{SD}	I _F = -1.5 A, V _{GS} = 0 V		-	-0.85	-1.2	V	
Body diode reverse recovery time	t _{rr}	I _F = -1.2 A, di/dt = 100A/us		-	9	18	ns	
Body diode reverse recovery charge	Q _{rr}			-	4	8	nC	
Reverse recovery fall time	ta			-	6.5	-	ns	
Reverse recovery rise time	t _b			-	2.5	-		
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.1	-	Α	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

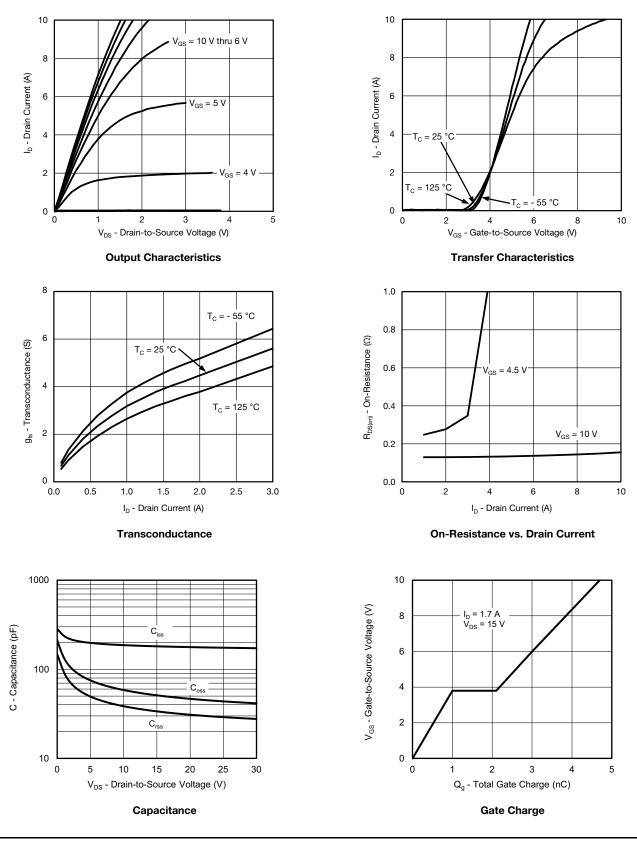
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



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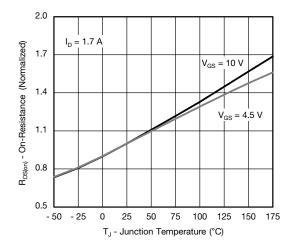
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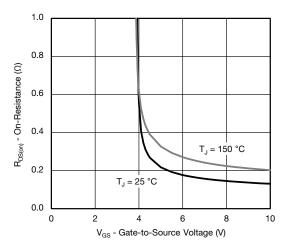
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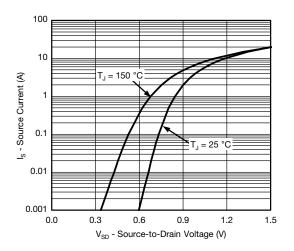
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



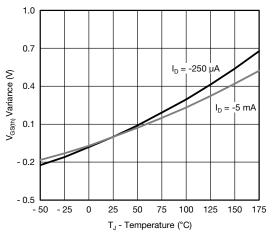
On-Resistance vs. Junction Temperature



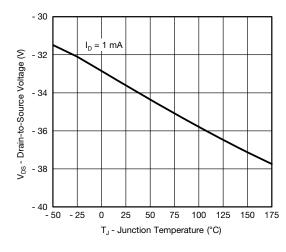
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature

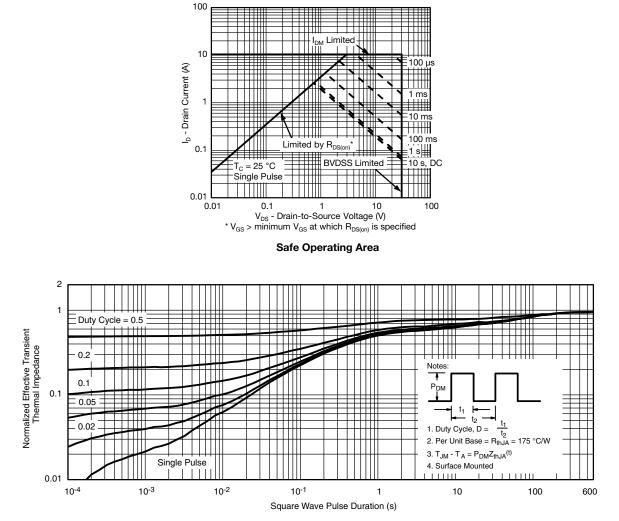
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



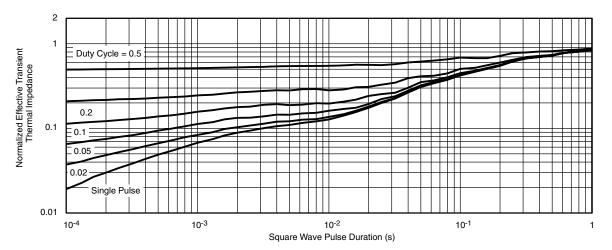
Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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